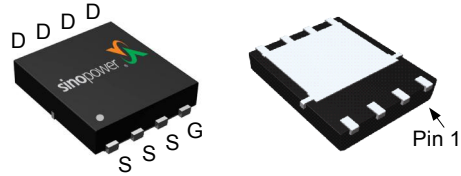


## N-Channel Enhancement Mode MOSFET

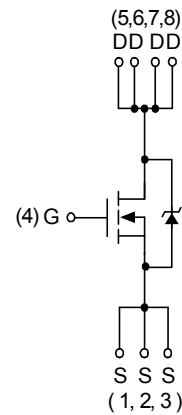
### Features

- 30V/100A,  
 $R_{DS(ON)} = 2.4m\Omega$  (max.) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 3.2m\Omega$  (max.) @  $V_{GS} = 4.5V$
- 100% UIS Tested
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)
- Integrated Schottky Diode

### Pin Description



DFN5x6-8

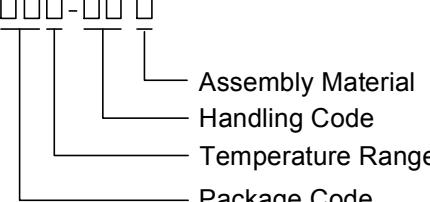



N-Channel MOSFET

### Applications

- Synchronous Rectifier for DC/DC Converters.
- NB Vcore low side switch.
- Networking Point of Load low side switch.
- Secondary side rectification.

### Ordering and Marking Information

<p>SM4382NA □□□-□□□</p>  <p>Assembly Material Handling Code Temperature Range Package Code</p>	<p>Package Code KP : DFN5x6-8 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape &amp; Reel (2500ea/reel) Assembly Material G : Halogen and Lead Free Device</p>
<p>SM4382NA KP :</p> 	<p>XXXXX - Date Code</p>

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b>			
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	
$I_S$	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 30	A
$I_D$	Continuous Drain Current	$T_C=25^\circ\text{C}$ 100 <sup>a</sup>	
		$T_C=100^\circ\text{C}$ 83	
$I_{DM}^b$	Pulse Drain Current	$T_C=25^\circ\text{C}$ 200	
$P_D$	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 62.5	W
		$T_C=100^\circ\text{C}$ 25	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State 2	$^\circ\text{C/W}$
$I_D$	Continuous Drain Current	$T_A=25^\circ\text{C}$ 34	A
		$T_A=70^\circ\text{C}$ 27	
$P_D$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 4.2	W
		$T_A=70^\circ\text{C}$ 2.7	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$ 15	$^\circ\text{C/W}$
		Steady State 30	
$I_{AS}^c$	Avalanche Current, Single pulse	$L=0.1\text{mH}$ 50	A
$E_{AS}^c$	Avalanche Energy, Single pulse	$L=0.1\text{mH}$ 125	mJ

Note a : Max. current is limited by bonding wire.

Note b : Pulse width limited by max. junction temperature.

Note c : UIS tested and pulse width limited by maximum junction temperature  $150^\circ\text{C}$  (initial temperature  $T_J=25^\circ\text{C}$ ).

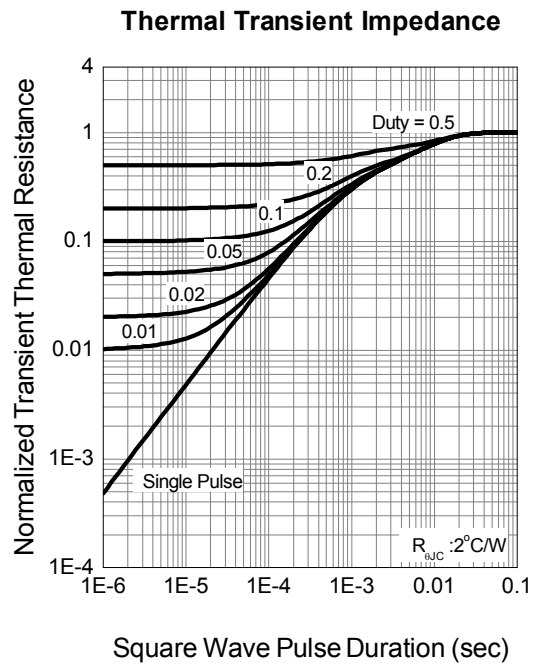
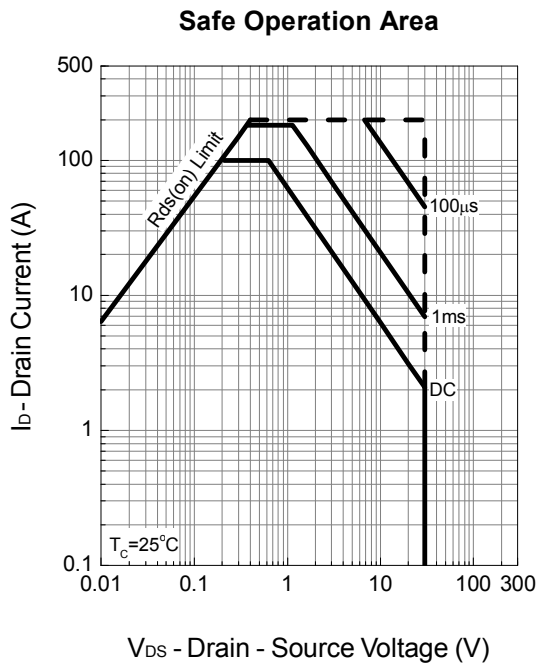
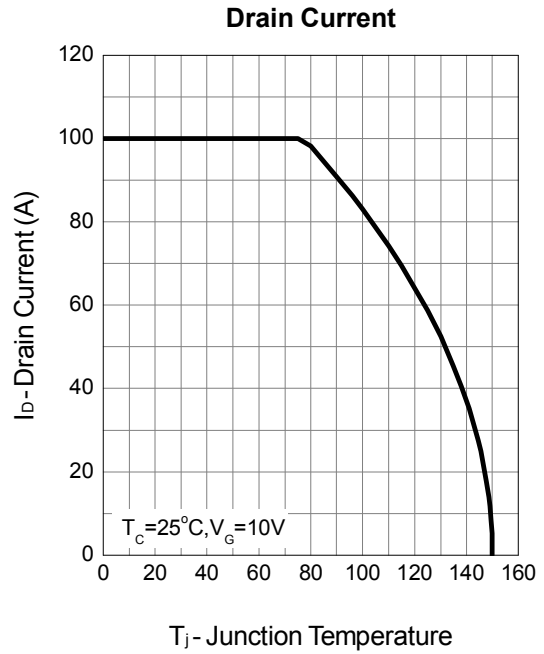
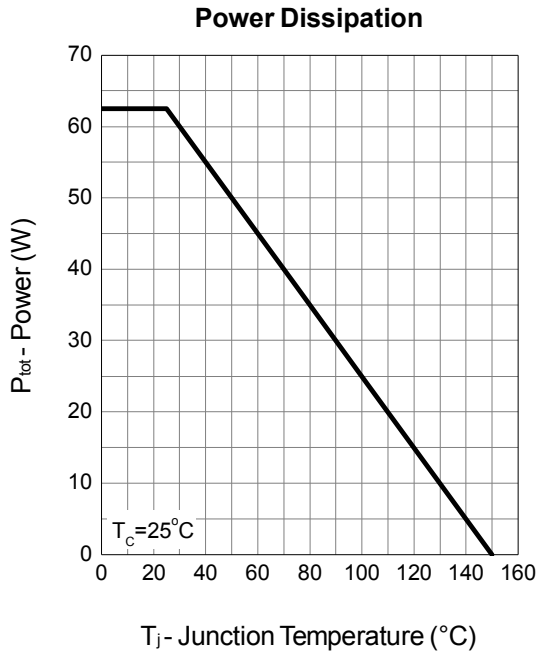
## Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24V, V_{GS}=0V$	-	-	50	$\mu A$
		$T_J=85^\circ C$	-	-	5	mA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1.4	1.7	2.5	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
$R_{DS(ON)}^d$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=20A$	-	1.9	2.4	m $\Omega$
		$T_J=125^\circ C$	-	2.9	-	
		$V_{GS}=4.5V, I_{DS}=15A$	-	2.4	3.2	
Gfs	Forward Transconductance	$V_{DS}=5V, I_{DS}=10A$	-	27	-	S
<b>Diode Characteristics</b>						
$V_{SD}^d$	Diode Forward Voltage	$I_{SD}=1A, V_{GS}=0V$	-	0.35	0.55	V
		$I_{SD}=20A, V_{GS}=0V$	-	0.75	1.1	
$t_{rr}$	Reverse Recovery Time	$I_{SD}=15A, di_{SD}/dt=100A/\mu s$	-	27	-	ns
$t_a$	Charge Time		-	13	-	
$t_b$	Discharge Time		-	14	-	
$Q_{rr}$	Reverse Recovery Charge		-	17	-	
<b>Dynamic Characteristics<sup>e</sup></b>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$	0.6	0.8	1.5	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=15V,$ Frequency=1.0MHz	2560	3200	3850	pF
$C_{oss}$	Output Capacitance		560	680	800	
$C_{riss}$	Reverse Transfer Capacitance		260	320	420	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=15V, R_L=15\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=6\Omega$	-	20	24	ns
$t_r$	Turn-on Rise Time		-	12	15	
$t_{d(OFF)}$	Turn-off Delay Time		-	69	78	
$t_f$	Turn-off Fall Time		-	29	34	
<b>Gate Charge Characteristics<sup>e</sup></b>						
$Q_g$	Total Gate Charge	$V_{DS}=15V, V_{GS}=10V,$ $I_{DS}=30A$	-	58	69	nC
$Q_g$	Total Gate Charge		-	26	31	
$Q_{gth}$	Threshold Gate Charge	$V_{DS}=15V, V_{GS}=4.5V,$ $I_{DS}=30A$	-	3.5	4.2	
$Q_{gs}$	Gate-Source Charge		-	9.5	11.4	
$Q_{gd}$	Gate-Drain Charge		-	11.4	14	

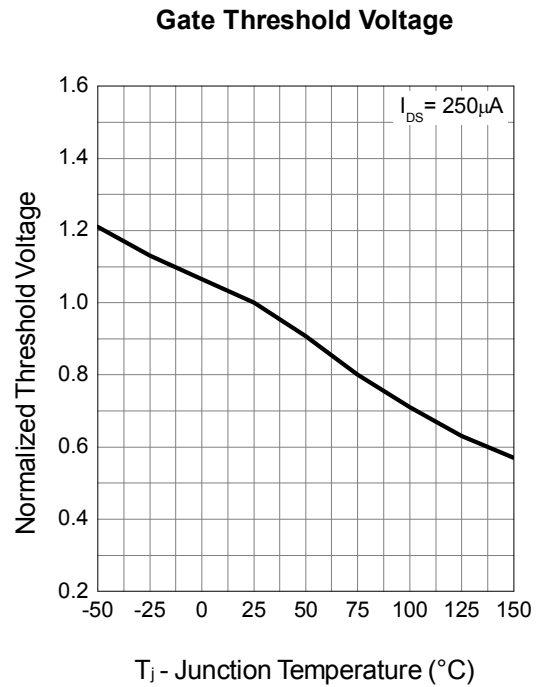
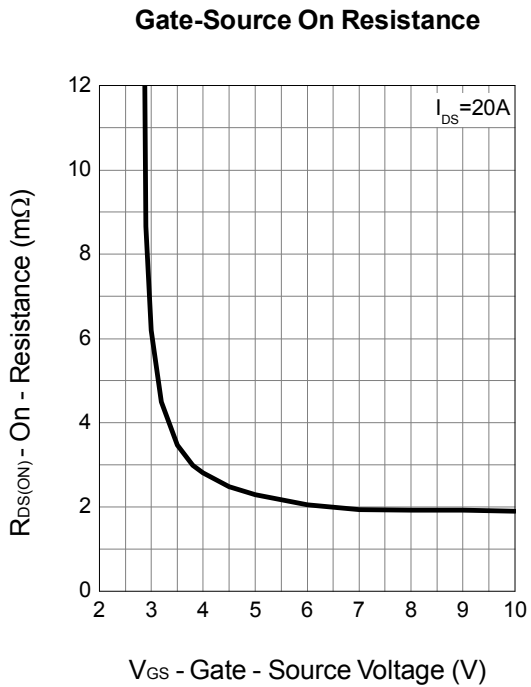
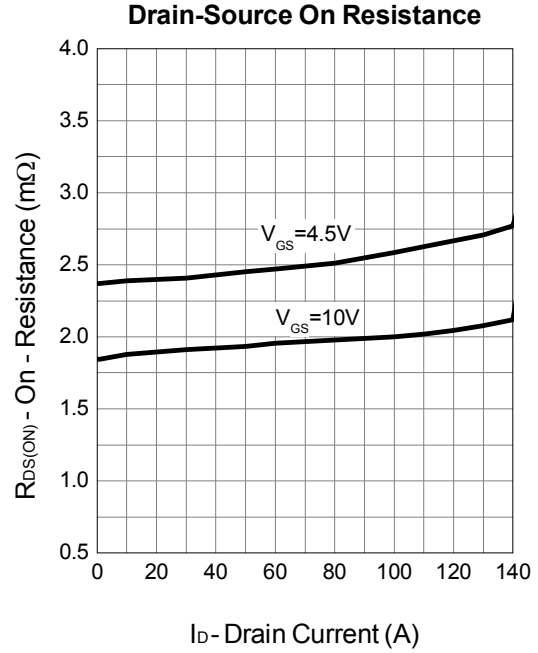
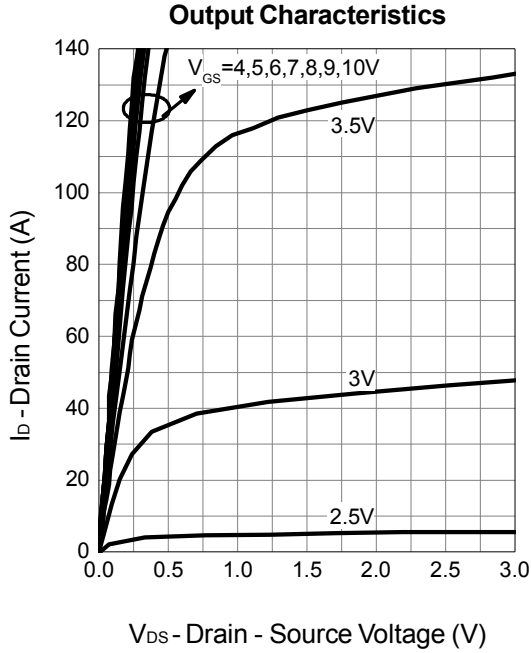
Note d : Pulse test; pulse width $\leq 300\mu s$ , duty cycle $\leq 2\%$ .

Note e : Guaranteed by design, not subject to production testing.

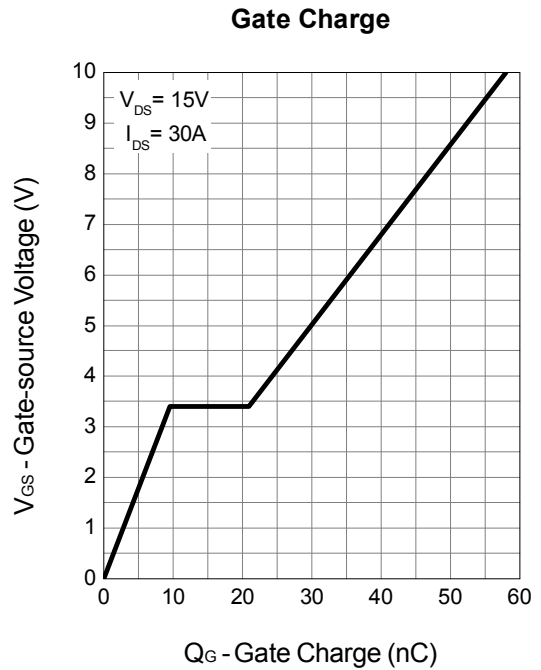
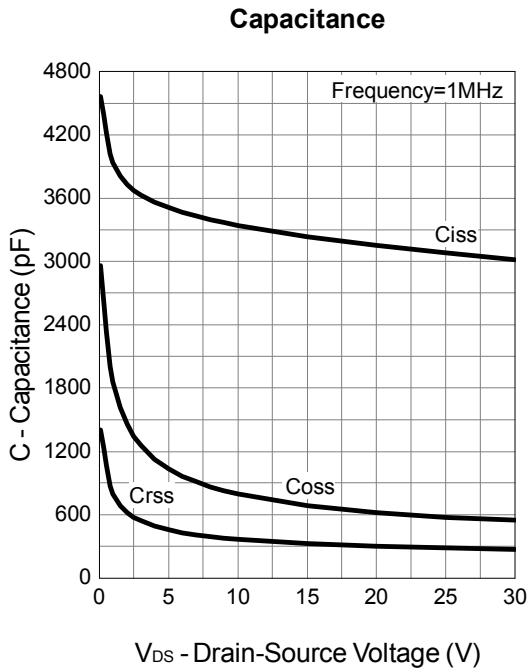
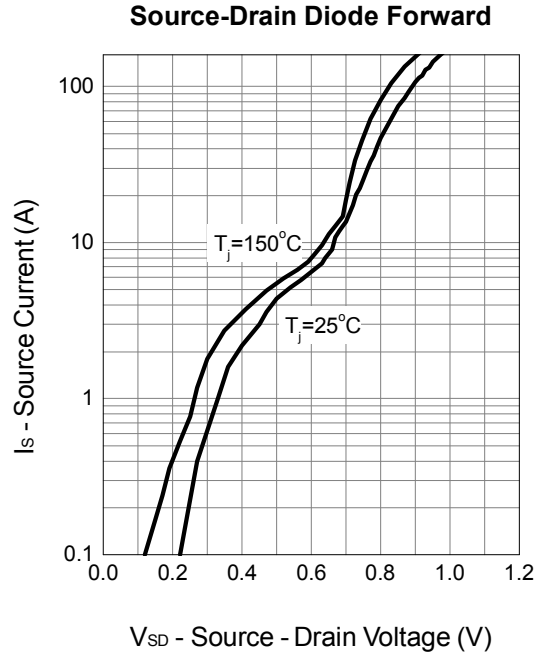
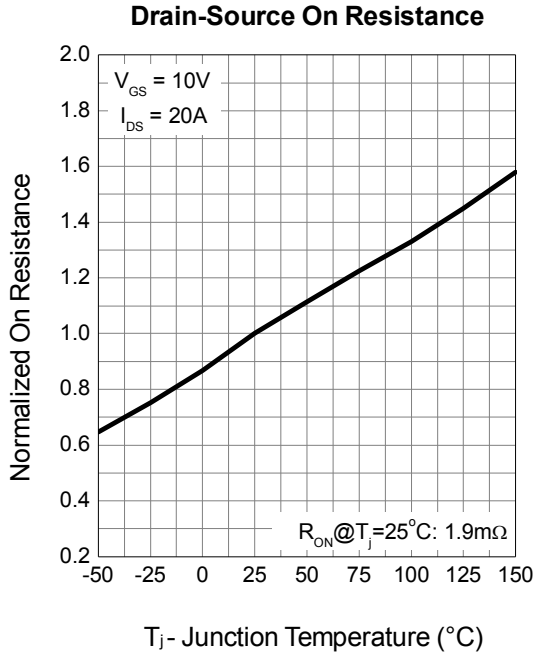
## Typical Operating Characteristics



Typical Operating Characteristics (Cont.)

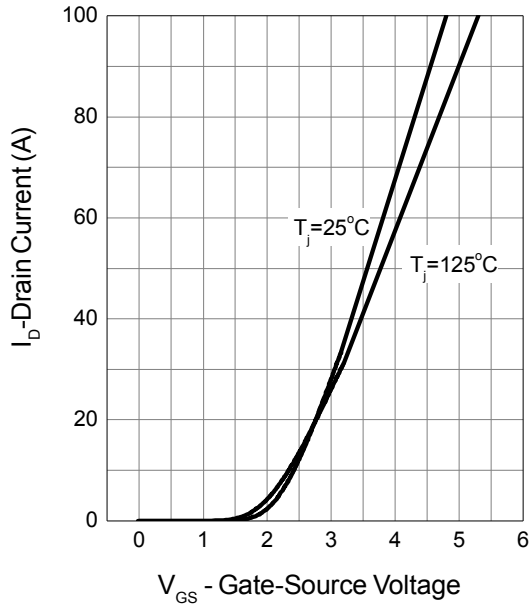


Typical Operating Characteristics (Cont.)



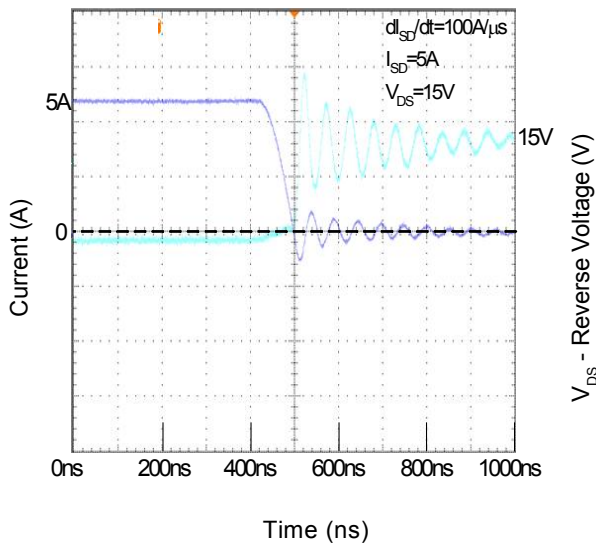
## Typical Operating Characteristics (Cont.)

Transfer Characteristics

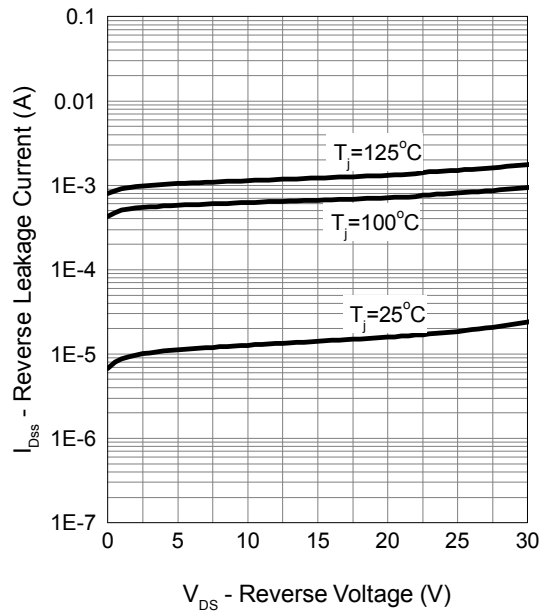


## Schottky Body Diode Characteristics

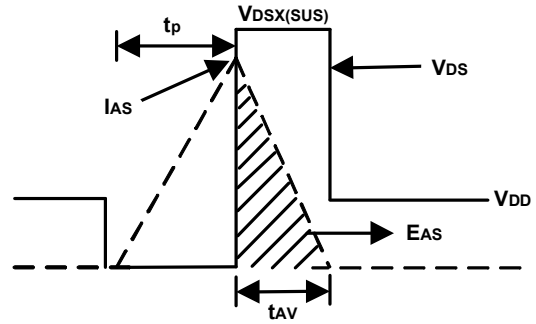
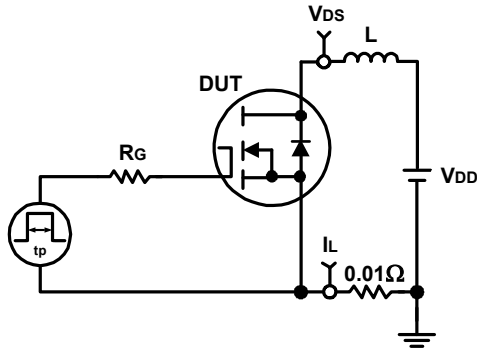
Body Diode Reverse Recovery Diode Characteristics



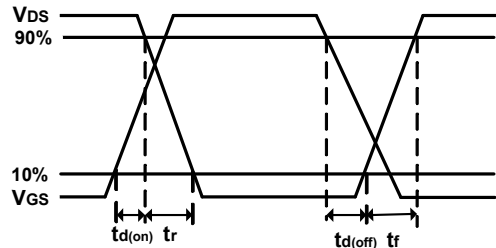
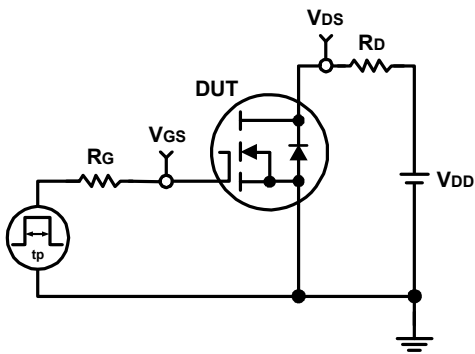
Body Diode Reverse Leakage Current



### Avalanche Test Circuit and Waveforms



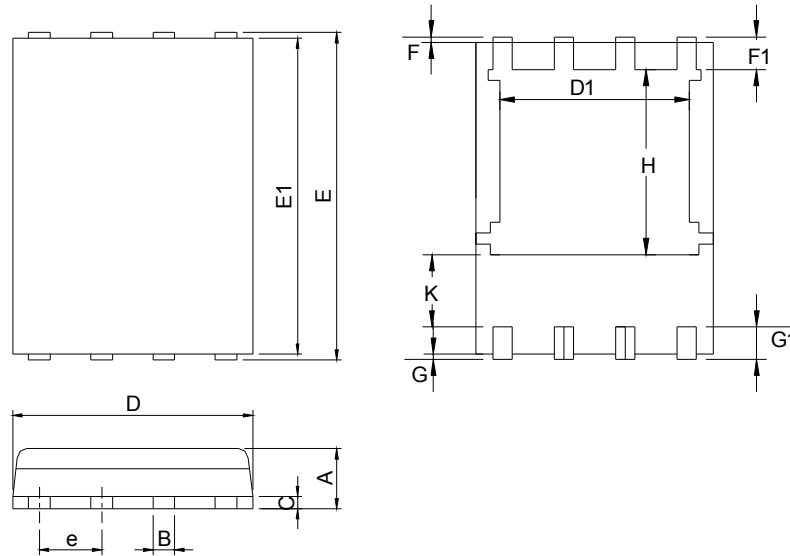
### Switching Time Test Circuit and Waveforms





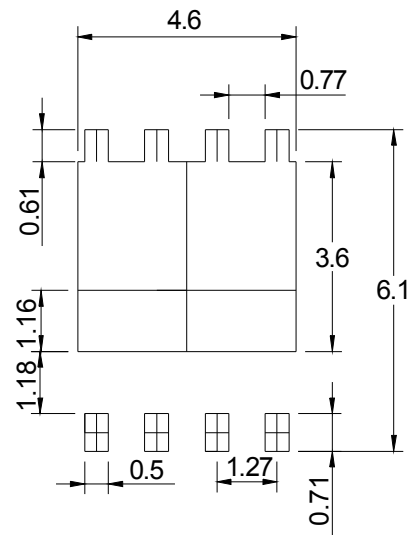
## Package Information

DFN5x6-8



DIMENSIONS	DFN5x6-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.20	0.035	0.047
B	0.3	0.51	0.012	0.020
C	0.19	0.25	0.007	0.010
D	4.80	5.30	0.189	0.209
D1	4.00	4.40	0.157	0.173
E	5.90	6.20	0.232	0.244
E1	5.50	5.80	0.217	0.228
e	1.27 BSC		0.050 BSC	
F	0.05	0.30	0.002	0.012
F1	0.35	0.75	0.014	0.030
G	0.05	0.30	0.002	0.012
G1	0.35	0.75	0.014	0.030
H	3.34	3.9	0.131	0.154
K	0.762	-	0.03	-

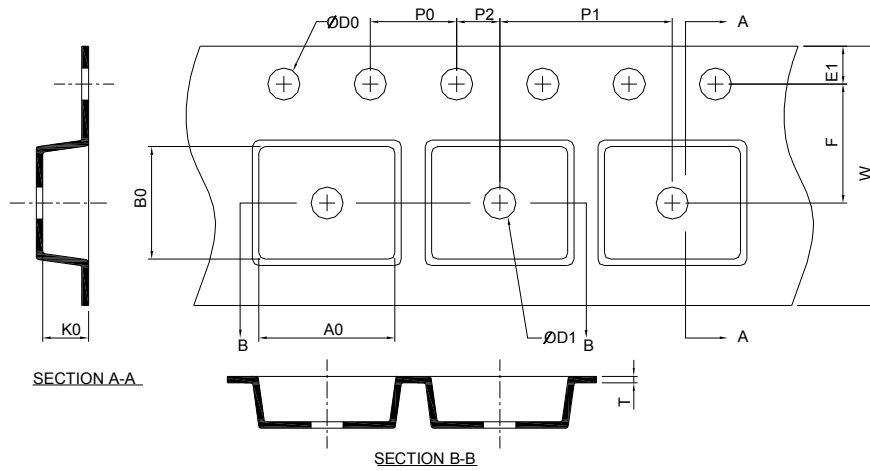
### RECOMMENDED LAND PATTERN



UNIT: mm

Note : 1.Dimension D, D1,D2 and E1 do not include mold flash or protrusions.  
Mold flash or protrusions shall not exceed 10 mil.

### Carrier Tape & Reel Dimensions

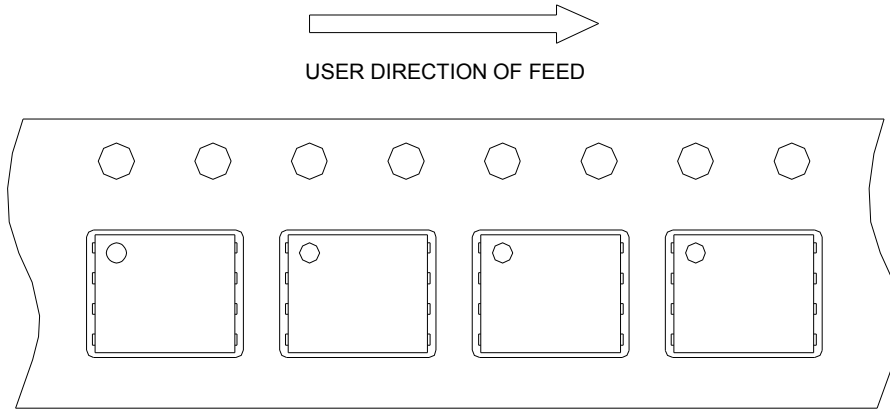


Application	A	H	T1	C	d	D	W	E1	F
DFN5x6-8	330.0±2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0±0.30	1.75±0.10	5.5±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0±0.10	8.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.4	6.5±0.20	5.3±0.20	1.4±0.20

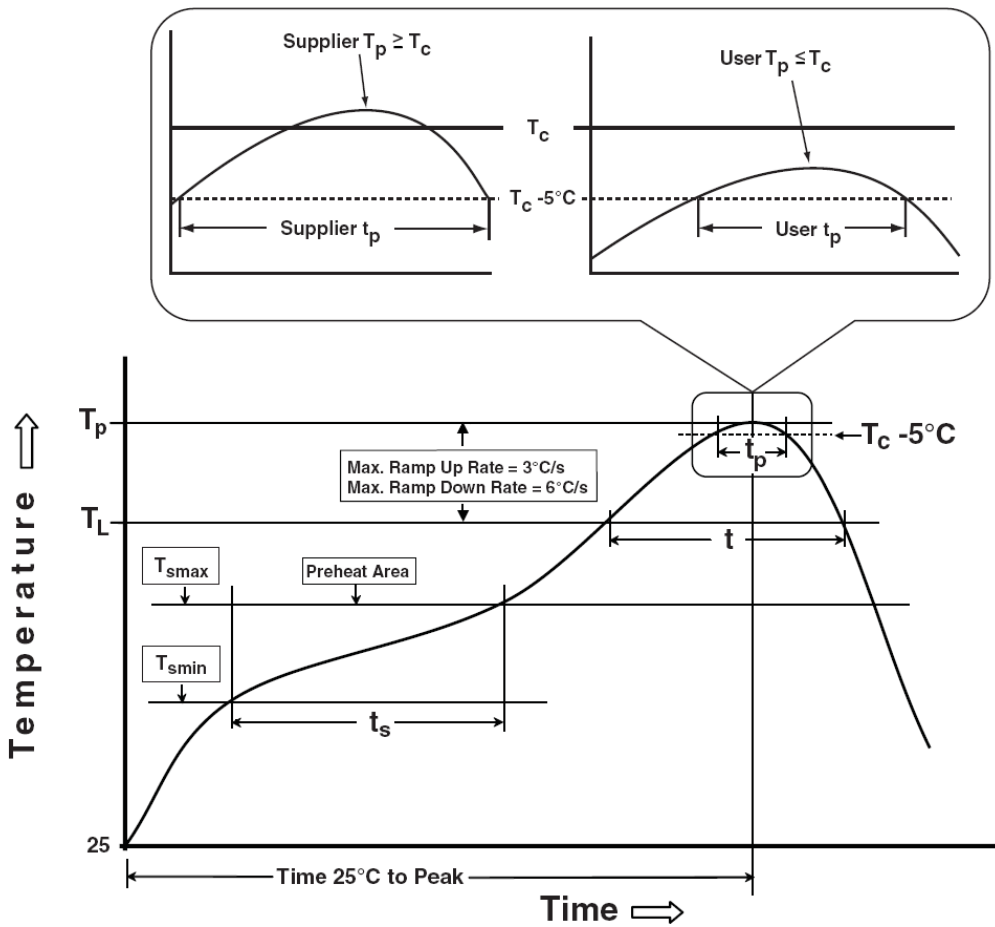
(mm)

## Taping Direction Information

DFN5x6-8



## Classification Profile



## Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
<b>Preheat &amp; Soak</b>		
Temperature min ( $T_{smin}$ )	100 °C	150 °C
Temperature max ( $T_{smax}$ )	150 °C	200 °C
Time ( $T_{smin}$ to $T_{smax}$ ) ( $t_s$ )	60-120 seconds	60-120 seconds
Average ramp-up rate ( $T_{smax}$ to $T_p$ )	3 °C/second max.	3°C/second max.
Liquidous temperature ( $T_L$ )	183 °C	217 °C
Time at liquidous ( $t_L$ )	60-150 seconds	60-150 seconds
Peak package body Temperature ( $T_p$ )*	See Classification Temp in table 1	See Classification Temp in table 2
Time ( $t_p$ )** within 5°C of the specified classification temperature ( $T_c$ )	20** seconds	30** seconds
Average ramp-down rate ( $T_p$ to $T_{smax}$ )	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature ( $T_p$ ) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature ( $t_p$ ) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures ( $T_c$ )

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures ( $T_c$ )

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

## Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ $T_{jmax}$
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ $T_{jmax}$
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

## Customer Service

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